Vishay Siliconix

E Series Power MOSFET

DESCRIPTION

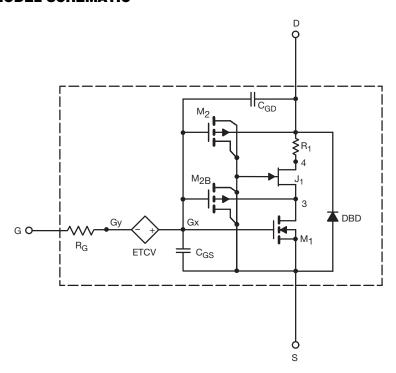
The attached SPICE model describes the typical electrical characteristics of the n-channel vertical DMOS. The subcircuit model is extracted and optimized over 25 °C to 150 °C temperature ranges under the pulsed 0 V to 15 V gate drive. The saturated output impedance is best fit at the gate bias near the threshold voltage.

A novel gate-to-drain feedback capacitance network is used to model the gate charge characteristics while avoiding convergence difficulties of the switched C_{gd} model. All model parameter values are optimized to provide a best fit to the measured electrical data and are not intended as an exact physical interpretation of the device.

CHARACTERISTICS

- N-channel vertical DMOS
- Macro model (subcircuit model)
- Level 3 MOS
- Apply for both linear and switching application
- Accurate over 25 °C to 150 °C temperature range
- · Model the gate charge

SUBCIRCUIT MODEL SCHEMATIC



Note

• This document is intended as a SPICE modeling guideline and does not constitute a commercial product datasheet. Designers should refer to the appropriate datasheet of the same number for guaranteed specification limits.



SPICE Device Model SiHB15N60E

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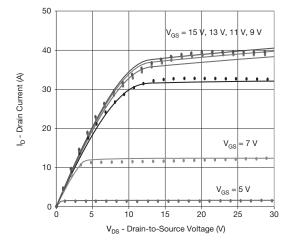
| SPECIFICATIONS (T _J = 25 °C, unless otherwise noted) | | | | | |
|------------------------------------------------------------------------|---------------------|-------------------------------------------------------------------------------------------------------------------|----------------|------------------|------|
| PARAMETER | SYMBOL | TEST CONDITIONS | SIMULATED DATA | MEASURED DATA | UNIT |
| Static | | | | | |
| Gate-Source Threshold Voltage | V _{GS(th)} | $V_{DS} = V_{GS}, I_D = 250 \mu A$ | 3 | - | V |
| Drain-Source On-State Resistance | R _{DS(on)} | $V_{GS} = 10 \text{ V}, I_D = 8 \text{ A}$ | 0.24 | 0.23 | Ω |
| Forward Transconductance | 9 _{fs} | $V_{DS} = 30 \text{ V}, I_{D} = 8 \text{ A}$ | 6 | 4.6 | S |
| Dynamic | | | | | |
| Input Capacitance | C _{iss} | V _{DS} = 100 V, V _{GS} = 0 V, f = 1 MHz | 1450 | 1350 | pF |
| Output Capacitance | Coss | | 138 | 70 | |
| Reverse Transfer Capacitance | C _{rss} | | 15 | 5 | |
| Total Gate Charge | Q_g | V _{DS} = 480 V, V _{GS} = 10 V, I _D = 8 A | 39 | 39 | nC |
| Gate-Source Charge | Q_{gs} | | 11 | 11 | |
| Gate-Drain Charge | Q_{gd} | | 17 | 17 | |
| Drain-Source Body Diode Characteristics | | | | | |
| Diode Forward Voltage | V_{SD} | $T_J = 25 ^{\circ}\text{C}, \ I_S = 8 \text{A}, \ V_{GS} = 0 \text{V}$ | 0.90 | - | V |
| Reverse Recovery Time | t _{rr} | $T_J = 25 ^{\circ}\text{C}$, $I_F = I_S = 8 \text{A}$, $dI/dt = 100 \text{A/}\mu\text{s}$, $V_R = 25 \text{V}$ | 400 | 410 | ns |
| Reverse Recovery Charge | Q_{rr} | | 7 | 5.4 | μC |

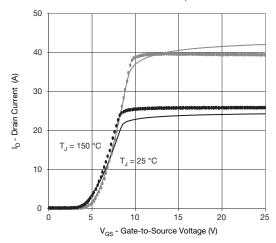


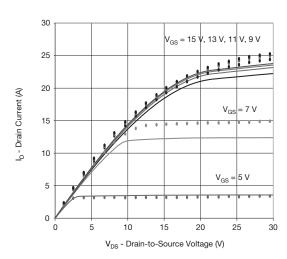
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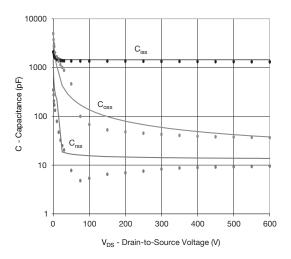
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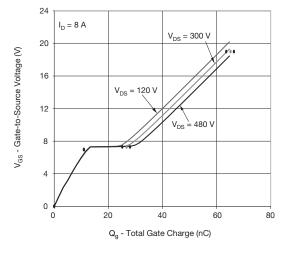
COMPARISON OF MODEL WITH MEASURED DATA ($T_J = 25$ °C, unless otherwise noted)

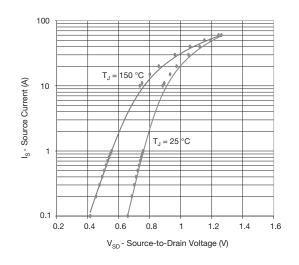












Note

Dots and squares represent measured data.
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